

8 AMP SILICON BRIDGE RECTIFIERS

FEATURES

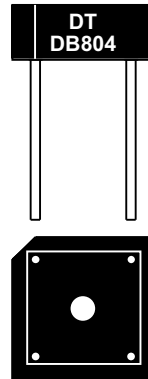
- **VOID FREE VACUUM DIE SOLDERING FOR MAXIMUM MECHANICAL STRENGTH AND HEAT DISSIPATION (Solder Voids: Typical < 2%, Max. < 10% of Die Area)**
- **BUILT-IN STRESS RELIEF MECHANISM FOR SUPERIOR RELIABILITY AND PERFORMANCE**
- **SURGE OVERLOAD RATING TO 400 AMPS PEAK**
- **UL RECOGNIZED - FILE #E124962**
- **RoHS COMPLIANT**

MECHANICAL DATA

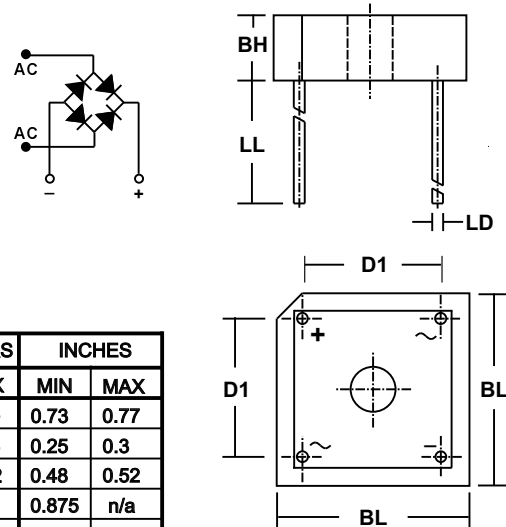
- **Case: Molded Epoxy (UL Flammability Rating 94V-0)**
- **Terminals: Round silver plated copper pins**
- **Soldering: Per MIL-STD 202 Method 208 guaranteed**
- **Polarity: Marked on side of case; positive lead at beveled corner**
- **Mounting Position: Any. Through hole provided for #6 screw**
- **Weight: 0.18 Ounces (5.4 Grams)**

MECHANICAL SPECIFICATION

ACTUAL SIZE



SERIES DB800-DB810 and ADB804-ADB808



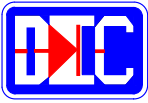
SYM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
BL	18.5	19.6	0.73	0.77
BH	6.4	7.6	0.25	0.3
D1	12.2	13.2	0.48	0.52
LL	22.2	n/a	0.875	n/a
LD	1.2	1.3	0.048	0.052

MAXIMUM RATINGS & ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60Hz, resistive or inductive load.
 For capacitive loads, derate current by 20%.

PARAMETER (TEST CONDITIONS)	SYMBOL	RATINGS										UNITS
		CONTROLLED AVALANCHE			NON-CONTROLLED AVALANCHE							
		ADB 804	ADB 806	ADB 808	DB 800	DB 801	DB 802	DB 804	DB 806	DB 808	DB 810	
Series Number												
Maximum DC Blocking Voltage	V _{RM}											
Working Peak Reverse Voltage	V _{RWM}	400	600	800	50	100	200	400	600	800	1000	VOLTS
Maximum Peak Recurrent Reverse Voltage	V _{R(RM)}											
RMS Reverse Voltage	V _{R(RMS)}	280	420	560	35	70	140	280	420	560	700	
Power Dissipation in V_(BR) Region for 100 μS Square Wave	P _{RM}	400			n/a							WATTS
Continuous Power Dissipation in V_(BR) Region @ T_{HS}=80° C (Heat Sink Temp)	P _R	2			n/a							
Thermal Energy (Rating for Fusing)	I ² t	64										AMPS ² SEC
Peak Forward Surge Current. Single 60Hz Half-Sine Wave Superimposed on Rated Load (JEDEC Method). T_J = 125° C	I _{FSM}	400										AMPS
Average Forward Rectified Current @ T_C = 50° C (Note 1) @ T_A = 50° C (Note 2)	I _O	10 8										
Junction Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150										°C
Minimum Avalanche Voltage	V _{(BR) Min}	See Note 4			n/a							VOLTS
Maximum Avalanche Voltage	V _{(BR) Max}	See Note 4			n/a							
Maximum Forward Voltage (Per Diode) at 4 Amps DC	V _{FM}	0.95 (Typ. 0.90)										
Maximum Reverse Current at Rated V_{RM} @ T_A = 25° C @ T_A = 125° C	I _{RM}	1 50										μA
Minimum Insulation Breakdown Voltage (Circuit to Case)	V _{ISO}	2000										VOLTS
Typical Thermal Resistance Junction to Ambient (Note 2) Junction to Case (Note 1)	R _{θJA} R _{θJC}	12 5										°C/W

NOTES: (1) Bridge mounted on 4.9" x 4.3" x 0.11" thick (12.4cm x 10.8cm x 0.3cm) aluminum plate
 (2) Bridge mounted on PC Board with 0.5" sq. (12mm sq.) copper pads and bridge lead length of 0.375" (9.5mm)
 (3) Bolt bridge on heat sink, using silicon thermal compound between bridge and mounting surface, for maximum heat transfer
 (4) These bridges exhibit the avalanche characteristic at breakdown. If your application requires a specific breakdown voltage range, please contact us.



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RATING & CHARACTERISTIC CURVES FOR SERIES DB800 - DB810 and SERIES ADB804 - ADB808

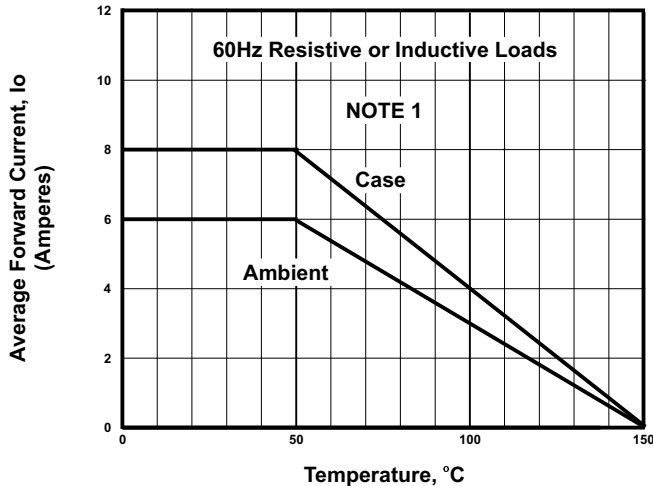


FIGURE 1. FORWARD CURRENT DERATING CURVE

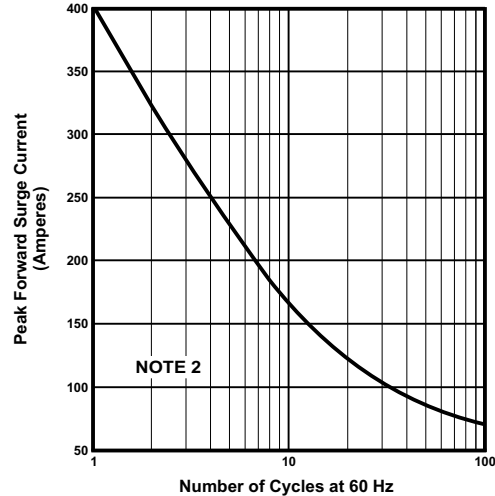


FIGURE 2. MAXIMUM NON-REPETITIVE SURGE CURRENT

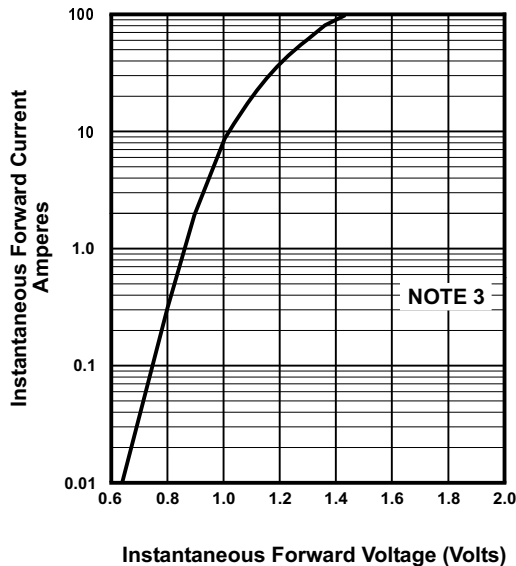


FIGURE 3. TYPICAL FORWARD CHARACTERISTIC PER DIODE

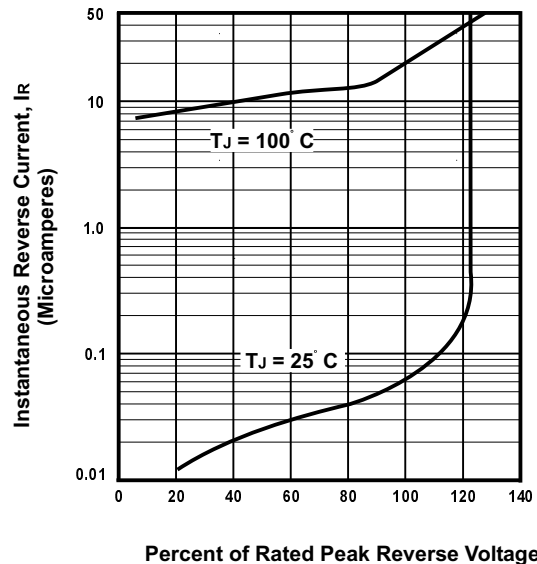


FIGURE 4. TYPICAL REVERSE CHARACTERISTICS

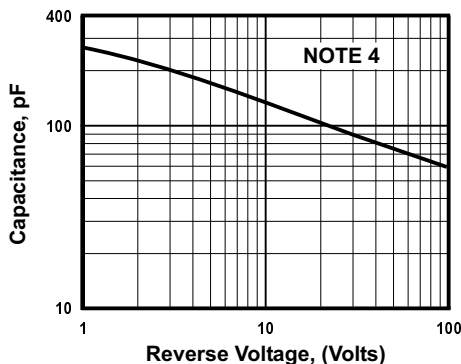


FIGURE 5. TYPICAL JUNCTION CAPACITANCE PER DIODE

NOTES

(1) Case Temperature, T_c . With Bridge Mounted on 4.9" x 4.3" x 0.11" Thick (12.4cm x 10.8cm x 0.3cm) Aluminum Plate

Ambient Temperature, T_A . With Bridge Mounted on PC Board With 0.5" Sq. (12mm Sq.) Copper Pads And Bridge Lead Length of 0.375" (9.5mm)

(2) $T_J = 125^\circ\text{C}$

(3) $T_J = 25^\circ\text{C}$; Pulse Width = 300 Sec; 1% Duty Cycle

(4) $T_J = 25^\circ\text{C}$; $f = 1\text{ MHz}$; $V_{sig} = 50\text{mVp-p}$